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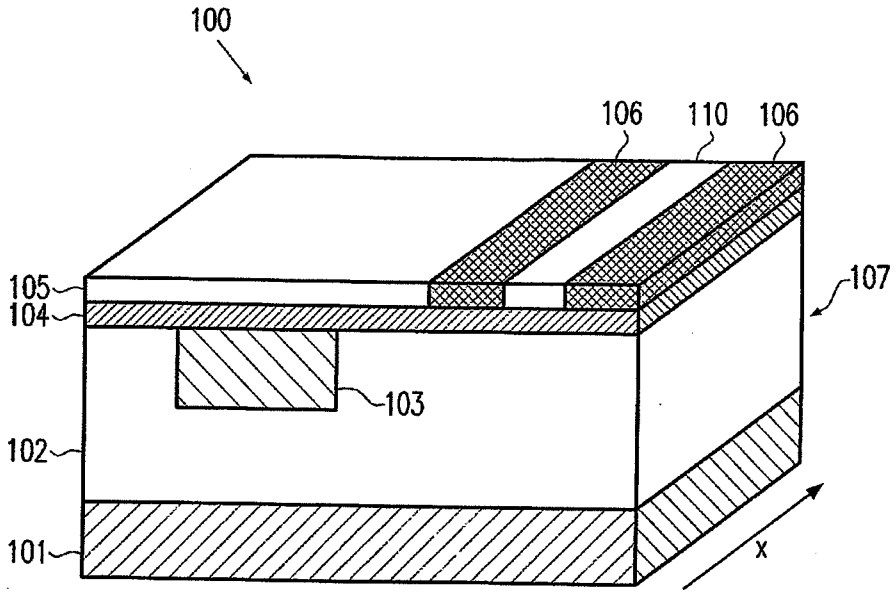
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(54) Title: SEMICONDUCTOR STRUCTURE COMPRISING A STRESS SENSITIVE ELEMENT AND METHOD OF MEASURING A STRESS IN A SEMICONDUCTOR STRUCTURE



(57) Abstract: A semiconductor structure comprises a stress sensitive element. A property of the stress sensitive element is representative of a stress in the semiconductor structure (100). Additionally, the semiconductor structure may comprise an electrical element (110). The stress sensitive element and the electrical element comprise portions of a common layer structure (107). Analyzers may be adapted to determine a property of the stress sensitive element being representative of a stress in the semiconductor structure (100) and a property of the electrical element (110). The property of the stress sensitive element maybe determined and the manufacturing process may be modified based on the determined property of the stress sensitive element. The property of the electrical element (110) may be related to the property of the stress sensitive element in order to investigate an influence of stress on the electrical element.

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